In the Claims:

Claim 1 (currently amended): A FET situated over a substrate, said FET comprising:

a channel situated in said substrate;

a first gate dielectric situated over said channel, said first gate dielectric having a first coefficient of thermal expansion;

a first gate electrode situated over said first gate dielectric, said first gate electrode having a second coefficient of thermal expansion;

wherein ~~said first gate dielectric is selected to have said first coefficient of thermal expansion and~~ said first gate electrode and said first gate dielectric are ~~is~~ selected such that ~~to have~~ said second coefficient of thermal expansion is greater than said first coefficient of thermal expansion so as to cause ~~a strain in said channel, thereby increasing~~ an increase in carrier mobility in said ~~FET~~ channel.

Claim 2 (canceled)

Claim 3 (currently amended): The FET of claim [[2]] 1 wherein said increase in said carrier mobility is caused by a tensile strain created in said channel.

Claims 4-5 (canceled)

Claim 6 (currently amended): The FET of claim 1 wherein said first gate dielectric has a thickness of between 10.0 Angstroms and 15.0 Angstroms ~~FET is a PFET~~.

Claims 7-8 (canceled)

Claim 9 (currently amended): A FET situated over a substrate, said FET comprising a channel situated in said substrate, a first gate dielectric situated over said channel, said first gate dielectric having a first coefficient of thermal expansion, a first gate electrode situated over said first gate dielectric, said first gate electrode having a second coefficient of thermal expansion, said FET being characterized in that:

said first gate dielectric ~~being selected to have said first coefficient of thermal expansion~~ and said first gate electrode being selected such that ~~to have~~ a difference between said first coefficient of thermal expansion and said second coefficient of thermal expansion ~~so as to cause a strain in said channel, thereby increasing~~ causes an increase in carrier mobility in said ~~FET~~ channel, wherein said first gate dielectric has a thickness of between 10.0 Angstroms and 15.0 Angstroms.

Claim 10 (original): The FET of claim 9 wherein said second coefficient of thermal expansion is greater than said first coefficient of thermal expansion so as to cause a tensile strain in said channel, said tensile strain causing said increase in said carrier mobility.

Claims 11-12 (canceled)

Claim 13 (original): The FET of claim 9 wherein said FET is a PFET, said first coefficient of thermal expansion being greater than said second coefficient of thermal expansion so as to cause a compressive strain in said channel, said compressive strain causing said increase in said carrier mobility.

Claim 14 (canceled)

Claim 15 (currently amended): A FET situated on a substrate, said FET comprising:

a channel situated in said substrate;

a gate stack situated over said channel;

a first gate dielectric situated in said gate stack, said first gate dielectric having a first coefficient of thermal expansion;

a first gate electrode situated over said first gate dielectric, said first gate electrode having a second coefficient of thermal expansion;

wherein ~~said first gate dielectric is selected to have said first coefficient of thermal expansion and~~ said first gate electrode and said first gate dielectric are ~~is~~ selected such that said first coefficient of thermal expansion is greater than ~~to have~~ said second coefficient of thermal expansion so as to cause ~~a compressive strain in said~~

~~channel, thereby increasing~~ an increase in carrier mobility in said ~~FET~~ channel, and wherein said FET is a PFET.

Claims 16-18 (canceled)

Claim 19 (currently amended): The FET of claim 15 wherein ~~said FET is a PFET,~~ said first coefficient of thermal expansion ~~being~~ is greater than said second coefficient of thermal expansion so as to cause ~~said compressive strain in said channel, said compressive strain causing~~ said increase in said carrier mobility by causing a compressive strain in said channel.

Claim 20 (canceled)

Claim 21 (new): The FET of claim 15 wherein said first gate dielectric has a thickness of between 10.0 Angstroms and 15.0 Angstroms.